

b) Amendments to the Claims

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--Claims 1-11 (Cancelled)

12. (New) A plasma treatment apparatus comprising:

A
a plurality of reactors each having an evacuable inside where at least one treatment substrate is set in, and having impedances different from each other;

a high-frequency power supply means for supplying high-frequency power into each reactor having been inside-evacuated, to cause glow discharge to take place in the reactor, wherein each of the reactors and the high-frequency power supply means are provided separably;

a plurality of impedance regulation means provided correspondingly to the impedances of the reactors in order to regulate impedances on the side of each reactor and on the side of the high-frequency power supply means; and

a moving means for moving the reactors.

13. (New) A plasma treatment apparatus comprising:

a plurality of reactors each having an evacuable inside where at least one treatment substrate is set in, and having impedances different from each other;

a high-frequency power supply means for supplying high-frequency power into each reactor having been inside-evacuated, to cause glow discharge to take place in the reactor; and

a plurality of impedance regulation means provided correspondingly to the impedances of the reactors in order to regulate impedances on the side of each

reactor and on the side of the high-frequency power supply means, wherein the high-frequency power supply means has an attachment part to which any one of the plurality of impedance regulation means is detachably mountable, and any one of the plurality of impedance regulation means is attached to the attachment part correspondingly to the impedances of the reactors.

14. (Re-presented - formerly dependent claim 7) The plasma treatment apparatus according to claim 12, wherein the impedance means is so provided in the high-frequency power supply means as to be able to be selected correspondingly to the impedances of the reactors.

15. (Re-presented - formerly dependent claim 8) The plasma treatment apparatus according to claim 14, wherein the high-frequency power supply means has a switch for selecting the impedance regulation means.

16. (Re-presented - formerly dependent claim 10) The plasma treatment apparatus according to claim 12, wherein each of the reactors and the high-frequency power supply means are provided separably and the reactors each have the impedance regulation means.--